

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-GSM850-251CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 90.97 V/m; Power Drift = 0.07 dB

PMF = 2.830 is applied.

E-field emissions = 203.4 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

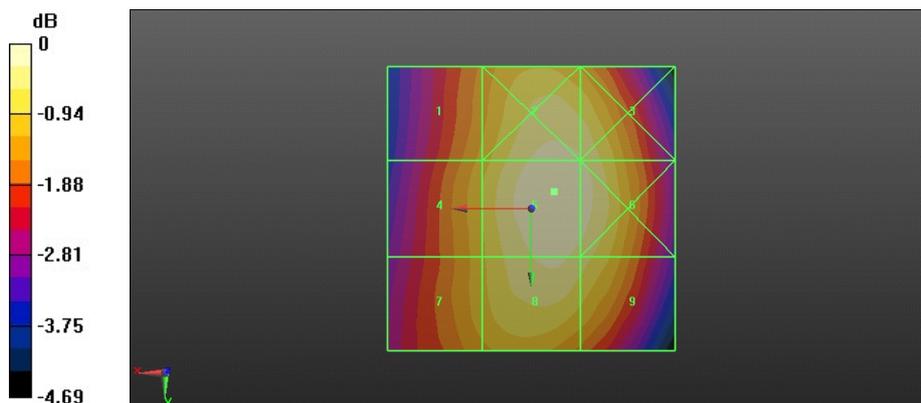
Grid 1 M3 179.1 V/m	Grid 2 M3 199.5 V/m	Grid 3 M3 197.0 V/m
Grid 4 M3 183.2 V/m	Grid 5 M3 203.4 V/m	Grid 6 M3 200.4 V/m
Grid 7 M3 181.4 V/m	Grid 8 M3 197.9 V/m	Grid 9 M3 193.1 V/m

Cursor:

Total = 203.4 V/m

E Category: M3

Location: -4, -3, 8.7 mm



0 dB = 203.4 V/m = 46.17 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-GSM850-190CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 85.83 V/m; Power Drift = -0.04 dB

PMF = 2.830 is applied.

E-field emissions = 189.9 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

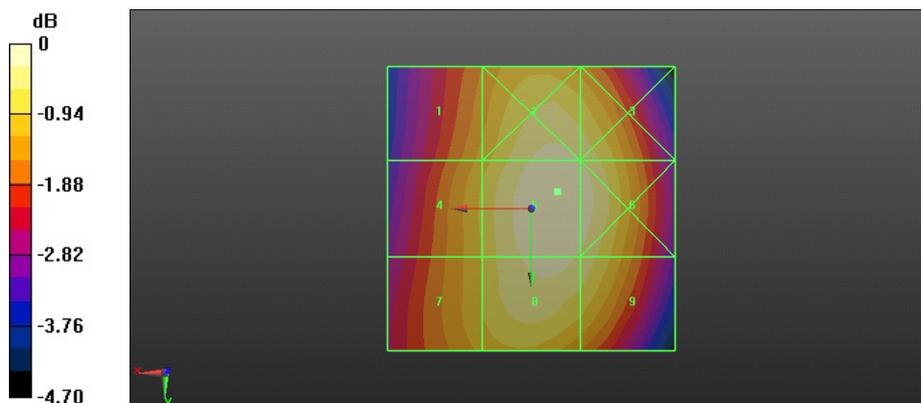
Grid 1 M3 167.4 V/m	Grid 2 M3 186.1 V/m	Grid 3 M3 182.9 V/m
Grid 4 M3 172.2 V/m	Grid 5 M3 189.9 V/m	Grid 6 M3 187.4 V/m
Grid 7 M3 171.2 V/m	Grid 8 M3 185.9 V/m	Grid 9 M3 182.3 V/m

Cursor:

Total = 189.9 V/m

E Category: M3

Location: -4.5, -3, 8.7 mm



0 dB = 189.9 V/m = 45.57 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-GSM850-128CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 75.65 V/m; Power Drift = -0.02 dB

PMF = 2.830 is applied.

E-field emissions = 168.2 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

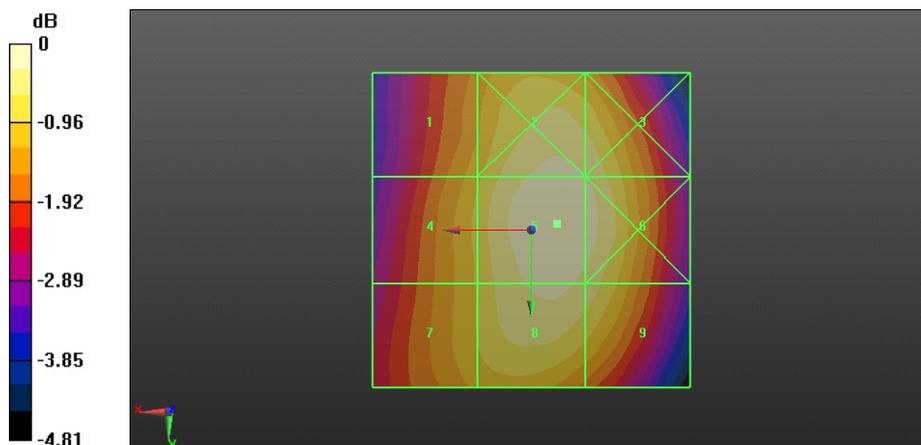
Grid 1 M4 149.1 V/m	Grid 2 M3 164.7 V/m	Grid 3 M3 162.3 V/m
Grid 4 M3 152.6 V/m	Grid 5 M3 168.2 V/m	Grid 6 M3 165.4 V/m
Grid 7 M3 151.3 V/m	Grid 8 M3 163.7 V/m	Grid 9 M3 160.3 V/m

Cursor:

Total = 168.2 V/m

E Category: M3

Location: -4, -1, 8.7 mm



0 dB = 168.2 V/m = 44.52 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-GSM1900-810CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 20.16 V/m; Power Drift = -0.06 dB

PMF = 2.860 is applied.

E-field emissions = 63.05 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

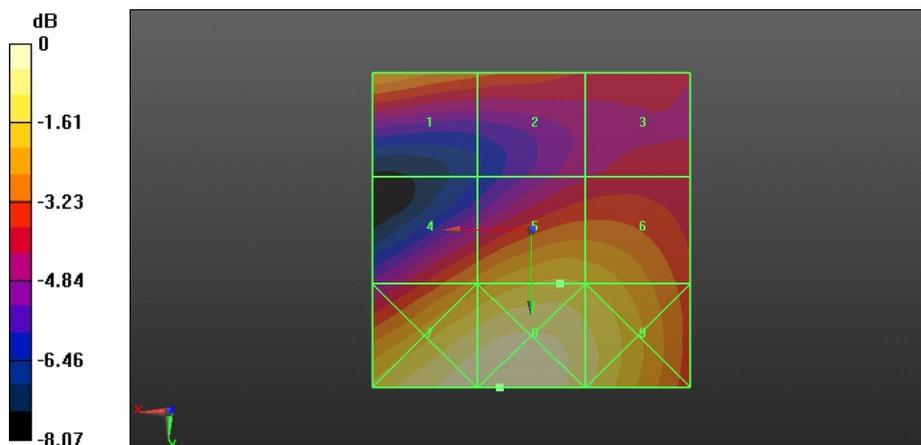
Grid 1 M3 58.84 V/m	Grid 2 M3 53.02 V/m	Grid 3 M3 48.34 V/m
Grid 4 M3 56.68 V/m	Grid 5 M3 63.05 V/m	Grid 6 M3 61.95 V/m
Grid 7 M3 74.12 V/m	Grid 8 M3 74.76 V/m	Grid 9 M3 67.97 V/m

Cursor:

Total = 74.76 V/m

E Category: M3

Location: 5, 25, 8.7 mm



0 dB = 74.76 V/m = 37.47 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-GSM1900-661CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 18.54 V/m; Power Drift = 0.01 dB

PMF = 2.860 is applied.

E-field emissions = 59.30 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

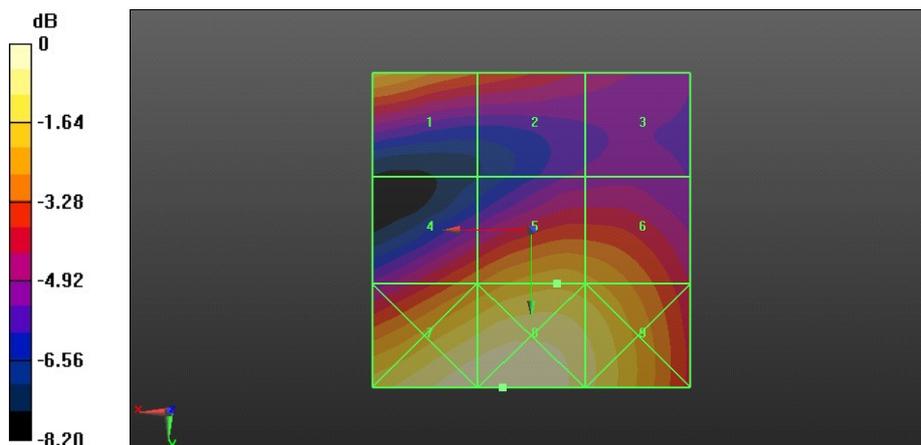
Grid 1 M3 58.33 V/m	Grid 2 M3 50.38 V/m	Grid 3 M4 43.87 V/m
Grid 4 M3 52.96 V/m	Grid 5 M3 59.30 V/m	Grid 6 M3 58.02 V/m
Grid 7 M3 72.15 V/m	Grid 8 M3 72.78 V/m	Grid 9 M3 65.97 V/m

Cursor:

Total = 72.78 V/m

E Category: M3

Location: 4.5, 25, 8.7 mm



0 dB = 72.78 V/m = 37.24 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-GSM1900-512CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 19.01 V/m; Power Drift = 0.02 dB

PMF = 2.860 is applied.

E-field emissions = 58.20 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

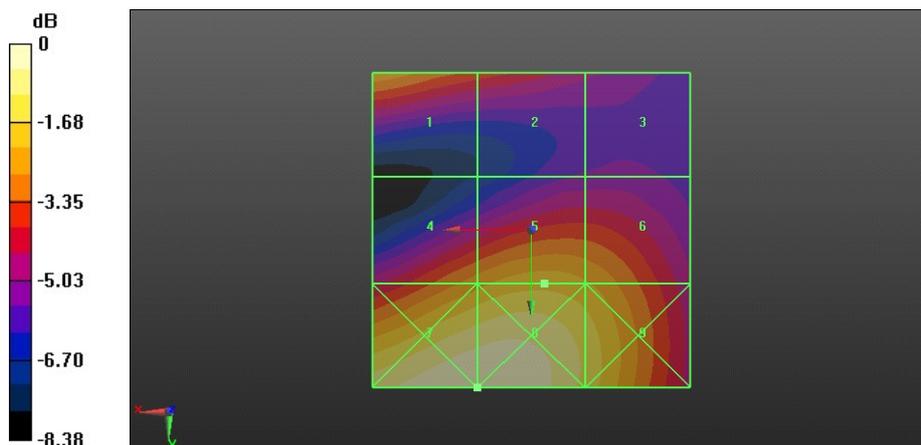
Grid 1 M3 55.19 V/m	Grid 2 M3 48.18 V/m	Grid 3 M4 41.37 V/m
Grid 4 M3 54.37 V/m	Grid 5 M3 58.20 V/m	Grid 6 M3 56.25 V/m
Grid 7 M3 72.02 V/m	Grid 8 M3 72.02 V/m	Grid 9 M3 62.45 V/m

Cursor:

Total = 72.02 V/m

E Category: M3

Location: 8.5, 25, 8.7 mm



0 dB = 72.02 V/m = 37.15 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-UMTS Band II-9538CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 25.69 V/m; Power Drift = 0.12 dB

PMF = 1.020 is applied.

E-field emissions = 28.91 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

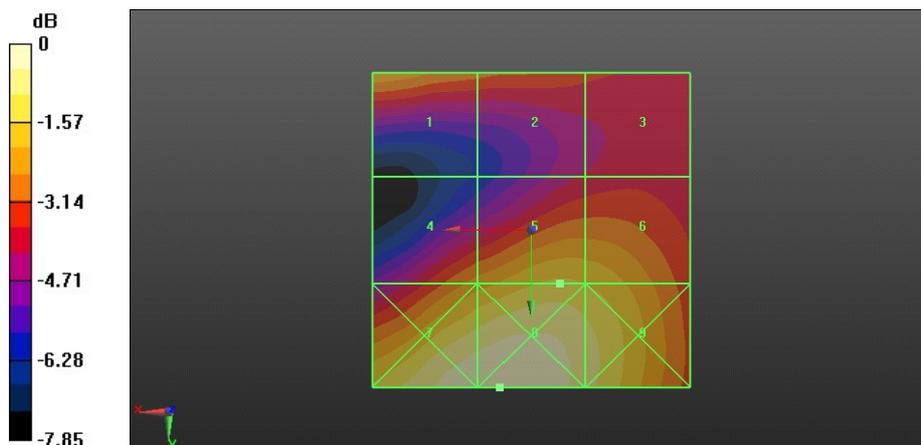
Grid 1 M4 26.83 V/m	Grid 2 M4 24.58 V/m	Grid 3 M4 22.93 V/m
Grid 4 M4 26.02 V/m	Grid 5 M4 28.91 V/m	Grid 6 M4 28.47 V/m
Grid 7 M4 33.91 V/m	Grid 8 M4 34.12 V/m	Grid 9 M4 31.21 V/m

Cursor:

Total = 34.12 V/m

E Category: M4

Location: 5, 25, 8.7 mm



0 dB = 34.12 V/m = 30.66 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-UMTS Band II-9400CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 22.59 V/m; Power Drift = -0.00 dB

PMF = 1.020 is applied.

E-field emissions = 25.47 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

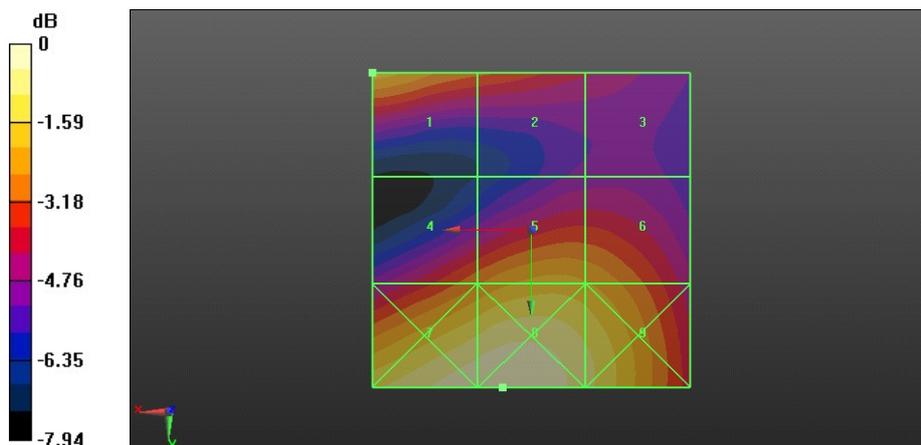
Grid 1 M4 25.47 V/m	Grid 2 M4 22.15 V/m	Grid 3 M4 19.45 V/m
Grid 4 M4 22.88 V/m	Grid 5 M4 25.27 V/m	Grid 6 M4 24.70 V/m
Grid 7 M4 31.01 V/m	Grid 8 M4 31.26 V/m	Grid 9 M4 28.33 V/m

Cursor:

Total = 31.26 V/m

E Category: M4

Location: 4.5, 25, 8.7 mm



0 dB = 31.26 V/m = 29.90 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-UMTS Band II-9262CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 25.21 V/m; Power Drift = 0.11 dB

PMF = 1.020 is applied.

E-field emissions = 27.51 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

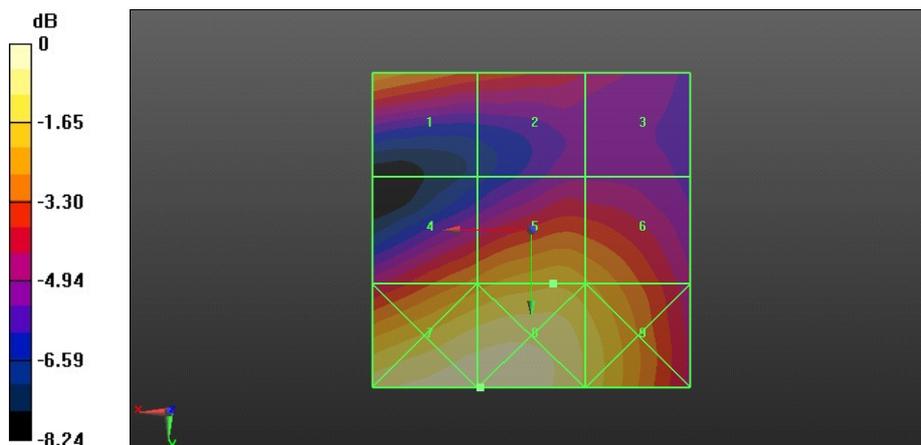
Grid 1 M4 25.66 V/m	Grid 2 M4 22.67 V/m	Grid 3 M4 20.14 V/m
Grid 4 M4 25.22 V/m	Grid 5 M4 27.51 V/m	Grid 6 M4 26.42 V/m
Grid 7 M4 33.54 V/m	Grid 8 M4 33.54 V/m	Grid 9 M4 29.36 V/m

Cursor:

Total = 33.54 V/m

E Category: M4

Location: 8, 25, 8.7 mm



0 dB = 33.54 V/m = 30.51 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-UMTS Band V-4233CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 80.93 V/m; Power Drift = -0.04 dB

PMF = 1.040 is applied.

E-field emissions = 66.79 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

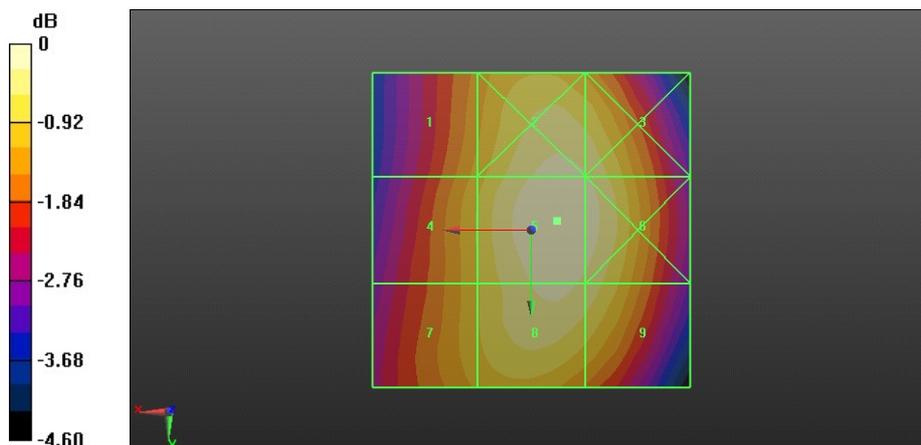
Grid 1 M4 59.01 V/m	Grid 2 M4 65.52 V/m	Grid 3 M4 64.68 V/m
Grid 4 M4 60.37 V/m	Grid 5 M4 66.79 V/m	Grid 6 M4 65.85 V/m
Grid 7 M4 59.89 V/m	Grid 8 M4 65.16 V/m	Grid 9 M4 63.93 V/m

Cursor:

Total = 66.79 V/m

E Category: M4

Location: -4, -1.5, 8.7 mm



0 dB = 66.79 V/m = 36.49 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-UMTS Band V-4182CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 81.40 V/m; Power Drift = -0.06 dB

PMF = 1.040 is applied.

E-field emissions = 66.91 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

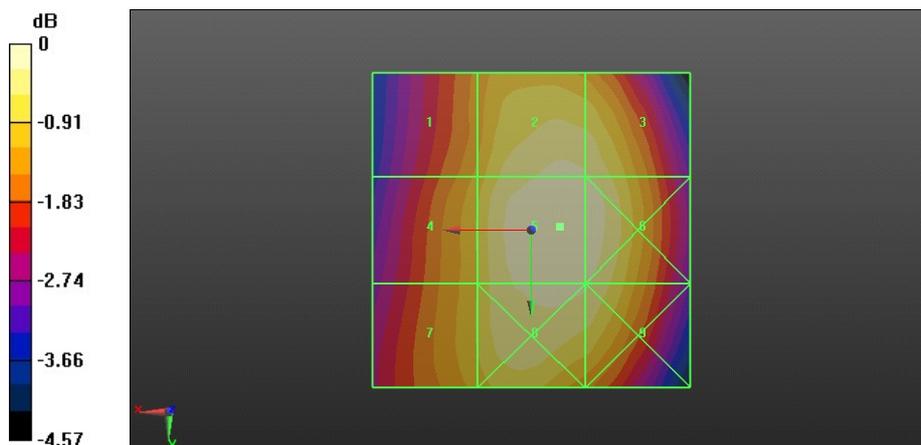
Grid 1 M4 58.91 V/m	Grid 2 M4 65.51 V/m	Grid 3 M4 64.90 V/m
Grid 4 M4 60.55 V/m	Grid 5 M4 66.91 V/m	Grid 6 M4 66.41 V/m
Grid 7 M4 60.51 V/m	Grid 8 M4 65.54 V/m	Grid 9 M4 64.91 V/m

Cursor:

Total = 66.91 V/m

E Category: M4

Location: -4.5, -0.5, 8.7 mm



0 dB = 66.91 V/m = 36.51 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H215G-UMTS Band V-4132CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 77.08 V/m; Power Drift = 0.01 dB

PMF = 1.040 is applied.

E-field emissions = 63.65 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

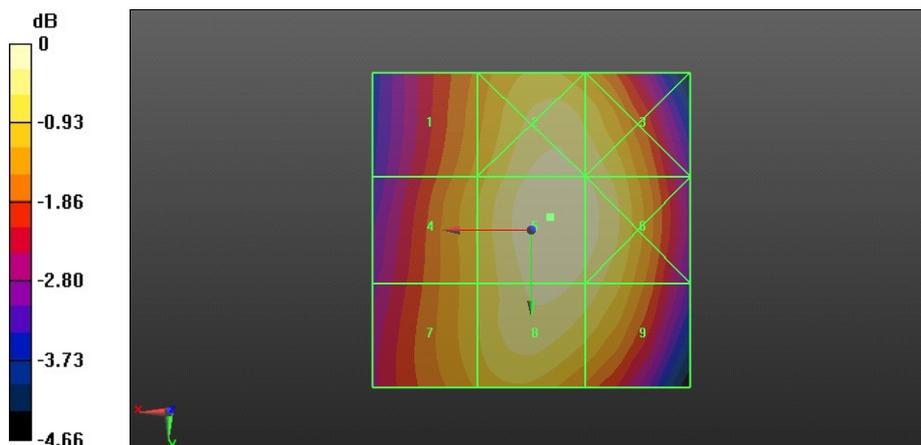
Grid 1 M4 56.12 V/m	Grid 2 M4 62.41 V/m	Grid 3 M4 61.48 V/m
Grid 4 M4 57.45 V/m	Grid 5 M4 63.65 V/m	Grid 6 M4 62.60 V/m
Grid 7 M4 57.07 V/m	Grid 8 M4 62.09 V/m	Grid 9 M4 60.73 V/m

Cursor:

Total = 63.65 V/m

E Category: M4

Location: -3, -2, 8.7 mm



0 dB = 63.65 V/m = 36.08 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-GSM850-251CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09100 A/m; Power Drift = -0.04 dB

PMF = 2.820 is applied.

H-field emissions = 0.3271 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

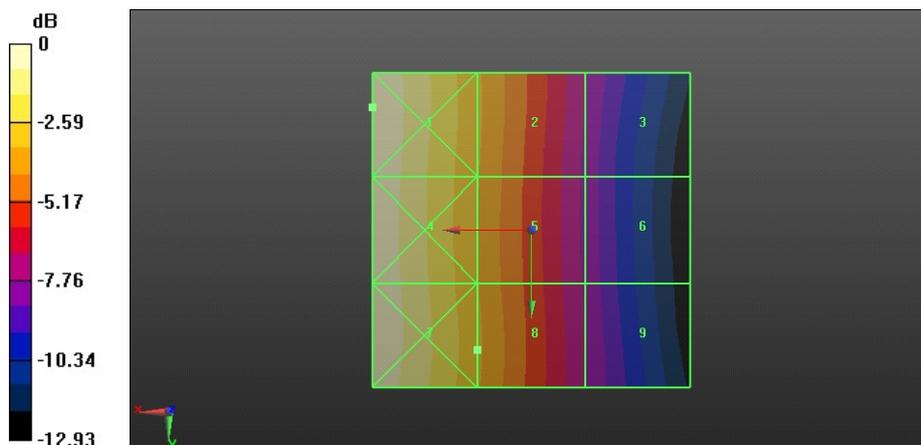
Grid 1 M3 0.475 A/m	Grid 2 M4 0.327 A/m	Grid 3 M4 0.196 A/m
Grid 4 M3 0.466 A/m	Grid 5 M4 0.323 A/m	Grid 6 M4 0.191 A/m
Grid 7 M3 0.473 A/m	Grid 8 M4 0.327 A/m	Grid 9 M4 0.196 A/m

Cursor:

Total = 0.4746 A/m

H Category: M3

Location: 25, -19.5, 8.7 mm



0 dB = 0.4746 A/m = -6.47 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-GSM850-190CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08100 A/m; Power Drift = -0.02 dB

PMF = 2.820 is applied.

H-field emissions = 0.3014 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

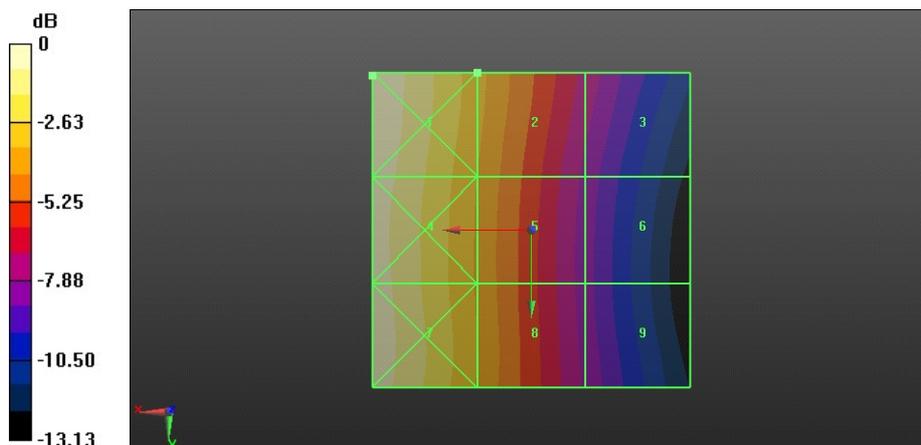
Grid 1 M4 0.433 A/m	Grid 2 M4 0.301 A/m	Grid 3 M4 0.188 A/m
Grid 4 M4 0.420 A/m	Grid 5 M4 0.289 A/m	Grid 6 M4 0.170 A/m
Grid 7 M4 0.420 A/m	Grid 8 M4 0.290 A/m	Grid 9 M4 0.172 A/m

Cursor:

Total = 0.4328 A/m

H Category: M4

Location: 25, -24.5, 8.7 mm



0 dB = 0.4328 A/m = -7.27 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-GSM850-128CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07600 A/m; Power Drift = -0.01 dB

PMF = 2.820 is applied.

H-field emissions = 0.2724 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

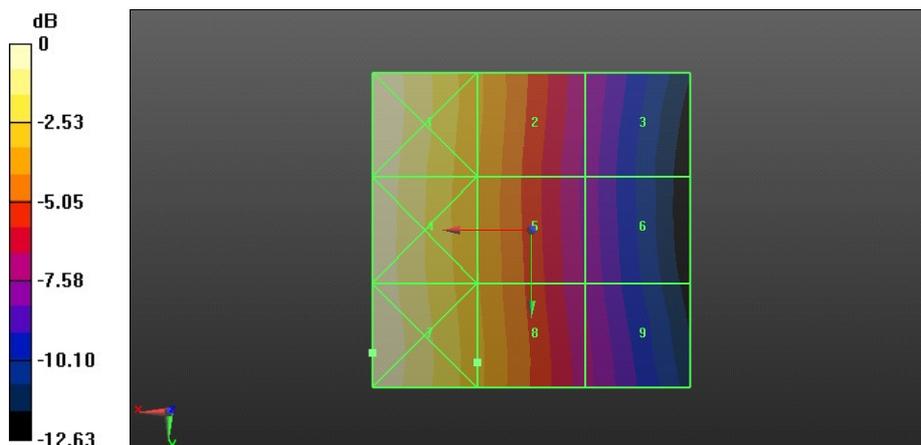
Grid 1 M4 0.387 A/m	Grid 2 M4 0.271 A/m	Grid 3 M4 0.164 A/m
Grid 4 M4 0.380 A/m	Grid 5 M4 0.267 A/m	Grid 6 M4 0.162 A/m
Grid 7 M4 0.389 A/m	Grid 8 M4 0.272 A/m	Grid 9 M4 0.169 A/m

Cursor:

Total = 0.3887 A/m

H Category: M4

Location: 25, 19.5, 8.7 mm



0 dB = 0.3887 A/m = -8.21 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-GSM1900-810CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06900 A/m; Power Drift = 0.02 dB

PMF = 2.830 is applied.

H-field emissions = 0.1953 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

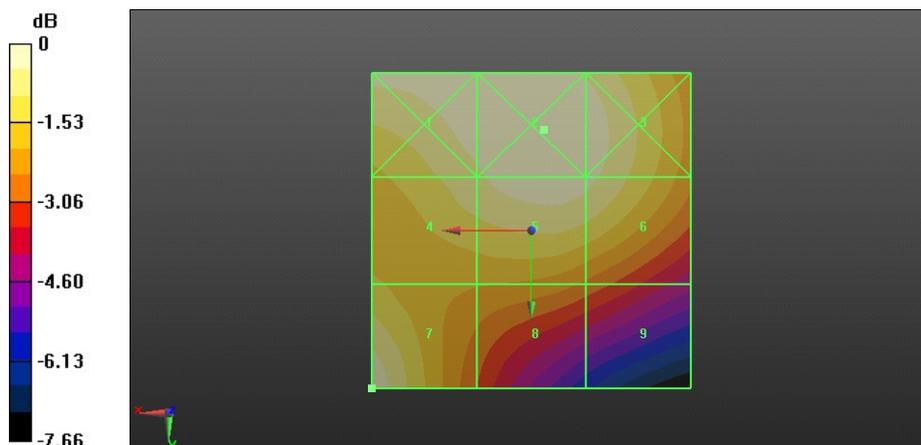
Grid 1 M3 0.190 A/m	Grid 2 M3 0.196 A/m	Grid 3 M3 0.192 A/m
Grid 4 M3 0.183 A/m	Grid 5 M3 0.192 A/m	Grid 6 M3 0.188 A/m
Grid 7 M3 0.195 A/m	Grid 8 M3 0.156 A/m	Grid 9 M3 0.144 A/m

Cursor:

Total = 0.1958 A/m

H Category: M3

Location: -2, -16, 8.7 mm



0 dB = 0.1958 A/m = -14.17 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-GSM1900-661CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05900 A/m; Power Drift = 0.05 dB

PMF = 2.830 is applied.

H-field emissions = 0.1693 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

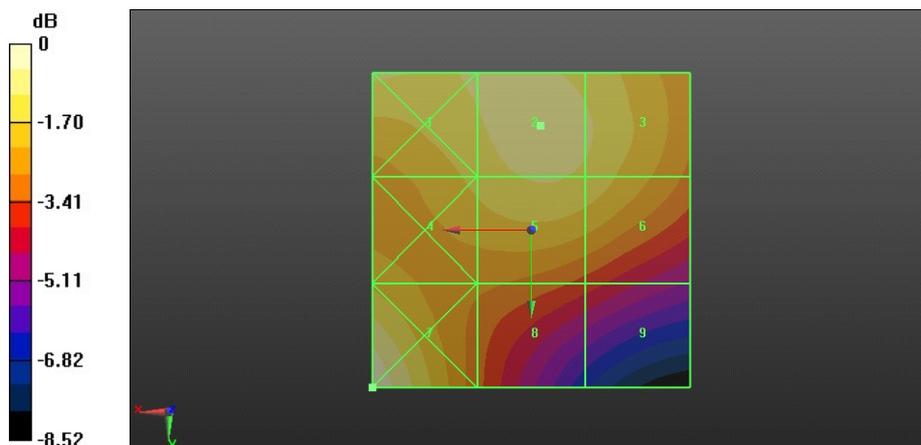
Grid 1 M3 0.167 A/m	Grid 2 M3 0.169 A/m	Grid 3 M3 0.166 A/m
Grid 4 M3 0.157 A/m	Grid 5 M3 0.165 A/m	Grid 6 M3 0.162 A/m
Grid 7 M3 0.187 A/m	Grid 8 M4 0.137 A/m	Grid 9 M4 0.123 A/m

Cursor:

Total = 0.1872 A/m

H Category: M3

Location: 25, 25, 8.7 mm



0 dB = 0.1872 A/m = -14.56 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-GSM1900-512CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.05800 A/m; Power Drift = 0.05 dB

PMF = 2.830 is applied.

H-field emissions = 0.1654 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

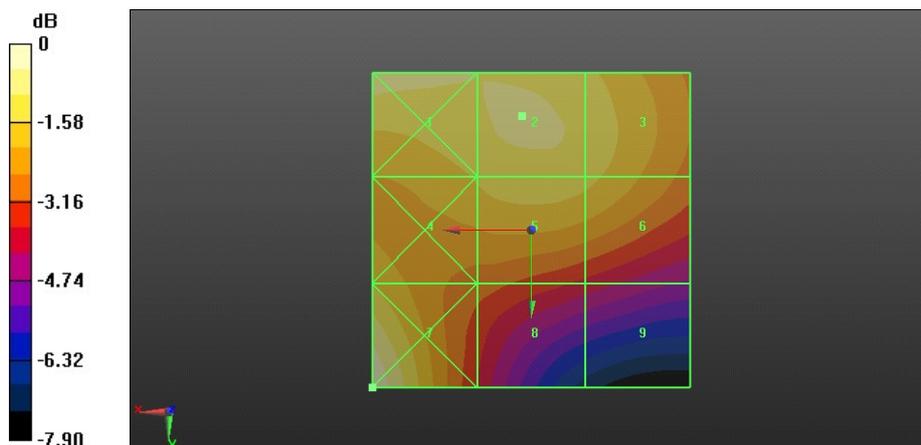
Grid 1 M3 0.170 A/m	Grid 2 M3 0.165 A/m	Grid 3 M3 0.161 A/m
Grid 4 M3 0.155 A/m	Grid 5 M3 0.160 A/m	Grid 6 M3 0.157 A/m
Grid 7 M3 0.185 A/m	Grid 8 M4 0.133 A/m	Grid 9 M4 0.119 A/m

Cursor:

Total = 0.1850 A/m

H Category: M3

Location: 25, 25, 8.7 mm



0 dB = 0.1850 A/m = -14.66 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-UMTS Band II-9538CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08600 A/m; Power Drift = -0.12 dB

PMF = 1.010 is applied.

H-field emissions = 0.08802 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

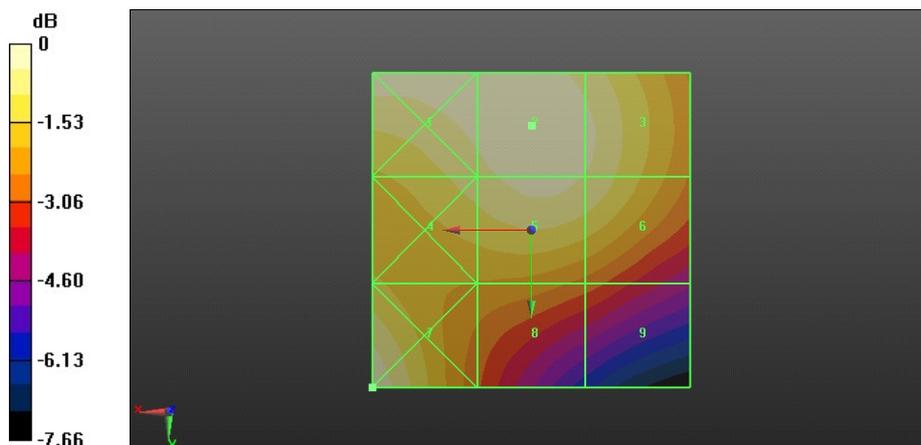
Grid 1 M4 0.087 A/m	Grid 2 M4 0.088 A/m	Grid 3 M4 0.085 A/m
Grid 4 M4 0.082 A/m	Grid 5 M4 0.086 A/m	Grid 6 M4 0.084 A/m
Grid 7 M4 0.089 A/m	Grid 8 M4 0.070 A/m	Grid 9 M4 0.065 A/m

Cursor:

Total = 0.08905 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.08905 A/m = -21.01 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-UMTS Band II-9400CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07200 A/m; Power Drift = 0.06 dB

PMF = 1.010 is applied.

H-field emissions = 0.07396 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

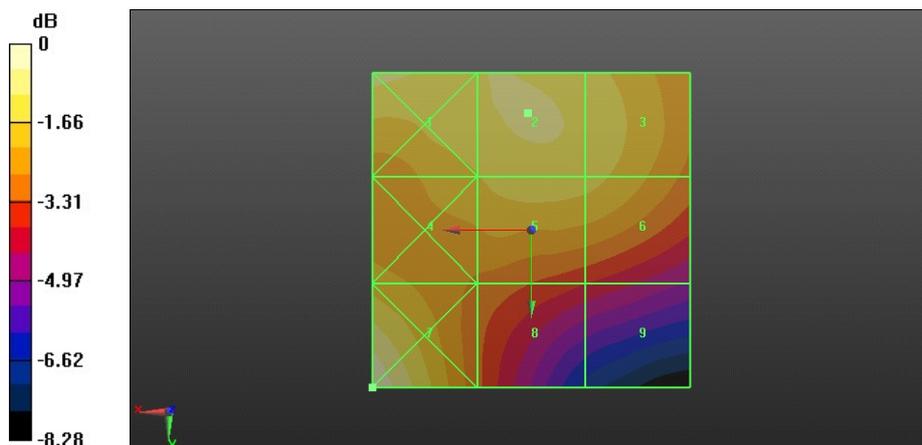
Grid 1 M4 0.076 A/m	Grid 2 M4 0.074 A/m	Grid 3 M4 0.073 A/m
Grid 4 M4 0.069 A/m	Grid 5 M4 0.072 A/m	Grid 6 M4 0.071 A/m
Grid 7 M4 0.083 A/m	Grid 8 M4 0.060 A/m	Grid 9 M4 0.054 A/m

Cursor:

Total = 0.08338 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.08338 A/m = -21.58 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-UMTS Band II-9262CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07800 A/m; Power Drift = -0.02 dB

PMF = 1.010 is applied.

H-field emissions = 0.07998 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

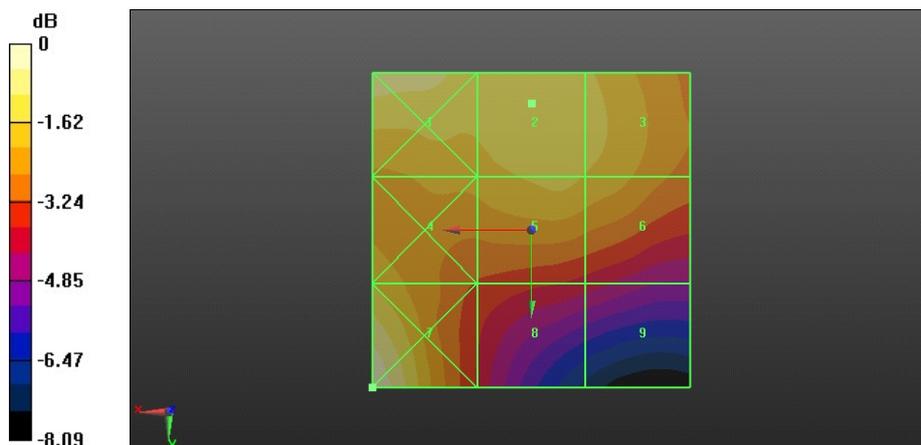
Grid 1 M4 0.085 A/m	Grid 2 M4 0.080 A/m	Grid 3 M4 0.078 A/m
Grid 4 M4 0.077 A/m	Grid 5 M4 0.078 A/m	Grid 6 M4 0.076 A/m
Grid 7 M4 0.092 A/m	Grid 8 M4 0.063 A/m	Grid 9 M4 0.058 A/m

Cursor:

Total = 0.09175 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.09175 A/m = -20.75 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-UMTS Band V-4233CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08100 A/m; Power Drift = -0.06 dB

PMF = 1.020 is applied.

H-field emissions = 0.1041 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

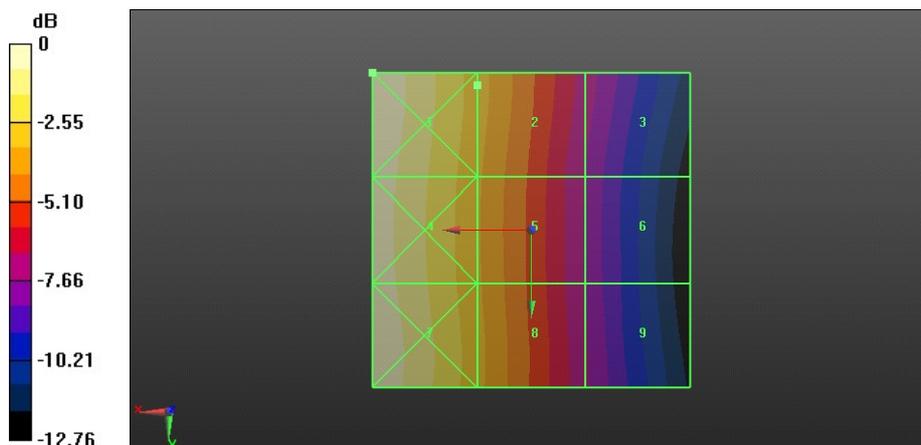
Grid 1 M4 0.147 A/m	Grid 2 M4 0.104 A/m	Grid 3 M4 0.064 A/m
Grid 4 M4 0.142 A/m	Grid 5 M4 0.101 A/m	Grid 6 M4 0.061 A/m
Grid 7 M4 0.145 A/m	Grid 8 M4 0.103 A/m	Grid 9 M4 0.062 A/m

Cursor:

Total = 0.1466 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1466 A/m = -16.67 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-UMTS Band V-4182CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07300 A/m; Power Drift = 0.03 dB

PMF = 1.020 is applied.

H-field emissions = 0.09976 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

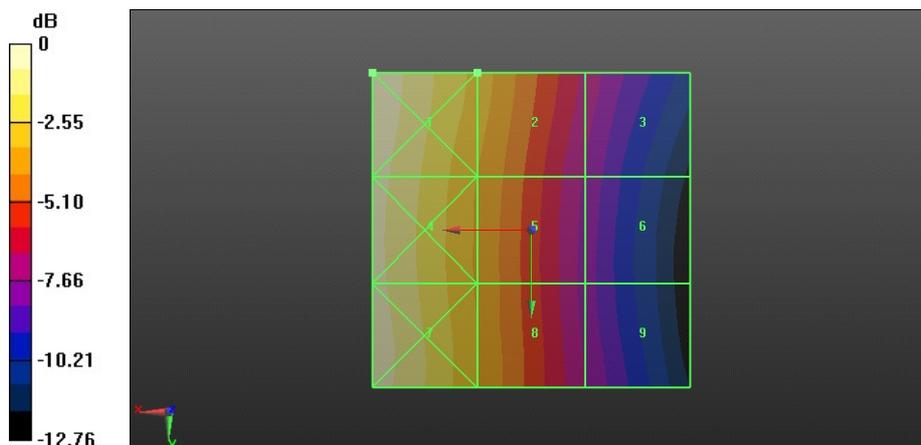
Grid 1 M4 0.139 A/m	Grid 2 M4 0.100 A/m	Grid 3 M4 0.062 A/m
Grid 4 M4 0.132 A/m	Grid 5 M4 0.094 A/m	Grid 6 M4 0.057 A/m
Grid 7 M4 0.135 A/m	Grid 8 M4 0.094 A/m	Grid 9 M4 0.058 A/m

Cursor:

Total = 0.1385 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1385 A/m = -17.17 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H215G-UMTS Band V-4132CH

DUT: H215G; Type: GSM/GPRS/UMTS/EDGE/HSDPA Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ S/m}$, $\epsilon_r = 1$; $\rho = 0 \text{ kg/m}^3$

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000 \text{ mm}$, $dy=0.5000 \text{ mm}$

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07600 A/m; Power Drift = -0.02 dB

PMF = 1.020 is applied.

H-field emissions = 0.09911 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

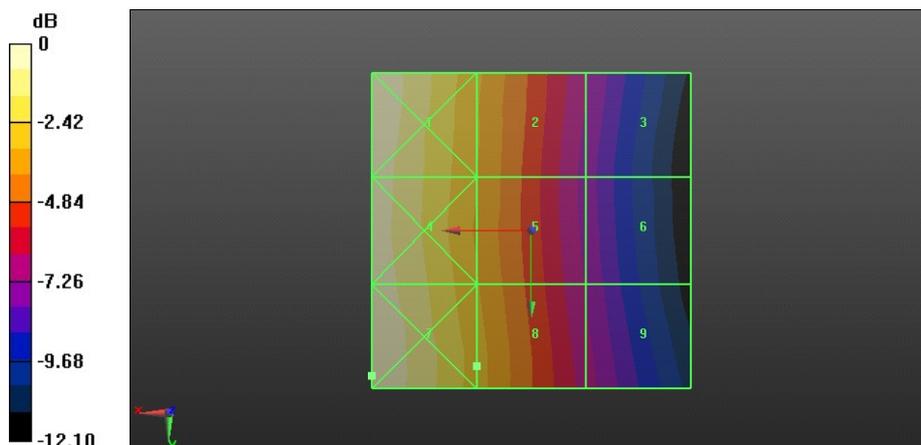
Grid 1 M4 0.137 A/m	Grid 2 M4 0.097 A/m	Grid 3 M4 0.060 A/m
Grid 4 M4 0.134 A/m	Grid 5 M4 0.096 A/m	Grid 6 M4 0.060 A/m
Grid 7 M4 0.137 A/m	Grid 8 M4 0.099 A/m	Grid 9 M4 0.063 A/m

Cursor:

Total = 0.1373 A/m

H Category: M4

Location: 25, 23, 8.7 mm



0 dB = 0.1373 A/m = -17.25 dBA/m